

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning at page 4, line 23, with the following rewritten paragraph:

FIG. 1 shows a MOS-type MOD-type power device and a drive system thereof in a tail-end circuit of a semiconductor apparatus according to a first embodiment of the present invention. For turning on the gate of a power device (e.g. IGBT) 1 associated with a freewheel diode D, two switches SWon 1, SWon 2 (or first and third switches) each composed of a transistor are inserted in series between a power supply VCC and the gate of the power device 1. A constant current device 4 is connected in parallel with the switch SWon 2.